

NCE P-Channel Enhancement Mode Power MOSFET

Description

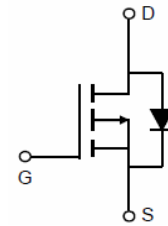
The NCE20P70G uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = -20V, I_D = -70A$
 - $R_{DS(ON)} < 3m\Omega @ V_{GS} = -4.5V$
 - $R_{DS(ON)} < 4m\Omega @ V_{GS} = -2.5V$
 - $R_{DS(ON)} < 8m\Omega @ V_{GS} = -1.8V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Load switch
- Battery protection



Schematic diagram



Pin Assignment



DFN5x6 -8L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE20P70G	NCE20P70G	DFN 5x6 -8L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	-70	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	-49.5	A
Pulsed Drain Current ^(Note 1)	I_{DM}	-280	A
Maximum Power Dissipation	P_D	130	W
Derating factor		1.04	W/ $^\circ C$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.96	$^\circ C/W$
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.6	-1.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-20A	-	2.3	3	mΩ
		V _{GS} =-2.5V, I _D =-20A	-	2.8	4	
		V _{GS} =-1.8V, I _D =-20A		3.8	8	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-20A	100	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V, F=1.0MHz	-	4950	-	PF
Output Capacitance	C _{oss}		-	380	-	PF
Reverse Transfer Capacitance	C _{rss}		-	290	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V, R _{GEN} =3Ω V _{GS} =-4.5V, R _L =0.5Ω	-	20	-	nS
Turn-on Rise Time	t _r		-	50	-	nS
Turn-Off Delay Time	t _{d(off)}		-	100	-	nS
Turn-Off Fall Time	t _f		-	40	-	nS
Total Gate Charge	Q _g	V _{DS} =-10V, I _D =-20A, V _{GS} =-4.5V	-	100	-	nC
Gate-Source Charge	Q _{gs}		-	21	-	nC
Gate-Drain Charge	Q _{gd}		-	32	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A	-	-	-1.2	V
Diode Forward Current	I _S		-	-	-70	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = -10A di/dt = 100A/μs (Note 3)	-	48	-	nS
Reverse Recovery Charge	Q _{rr}		-	55	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

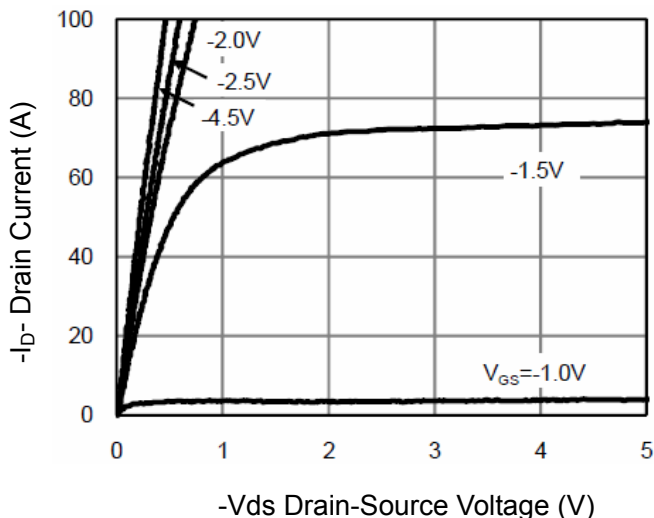


Figure 1 Output Characteristics

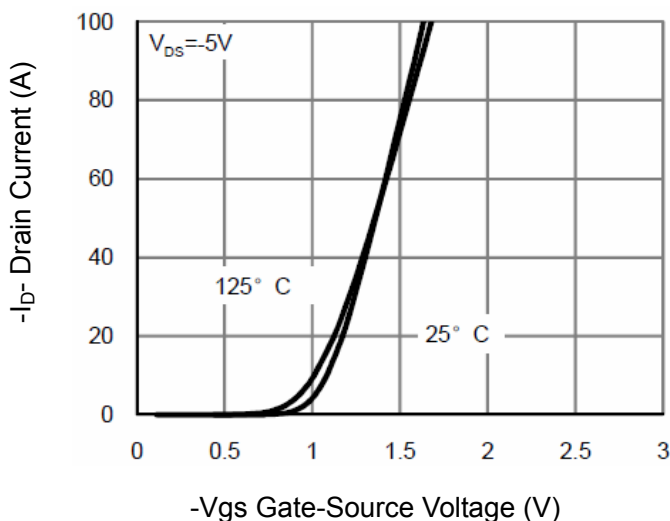


Figure 2 Transfer Characteristics

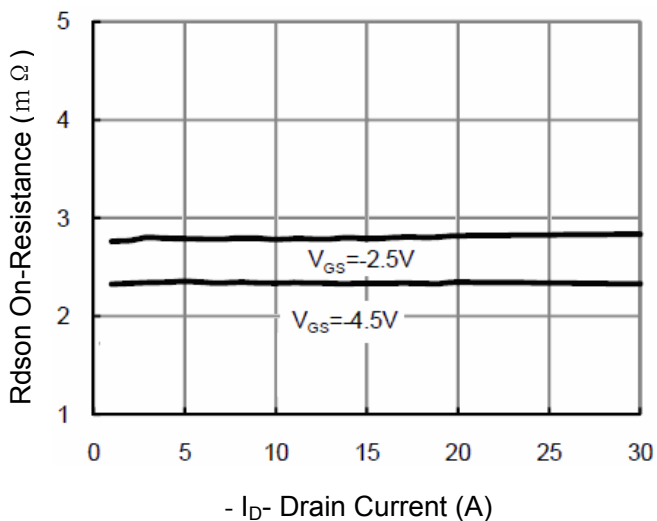


Figure 3 $R_{DS(on)}$ - Drain Current

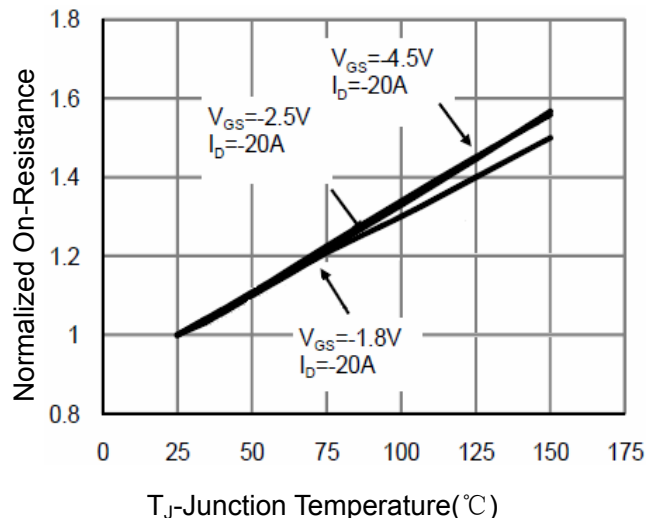


Figure 4 $R_{DS(on)}$ -Junction Temperature

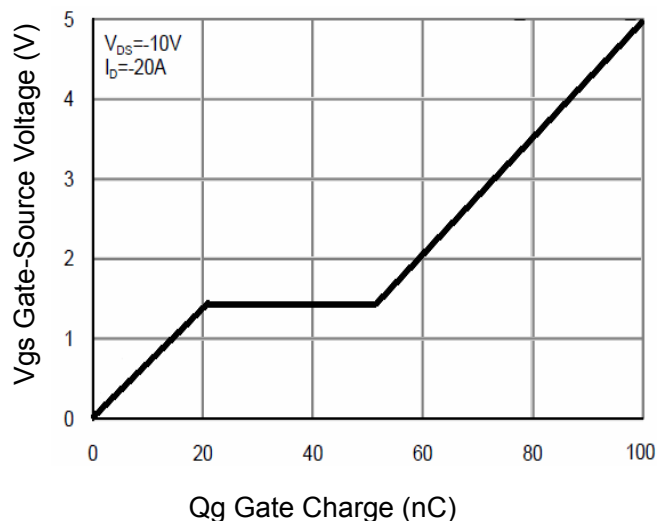


Figure 5 Gate Charge

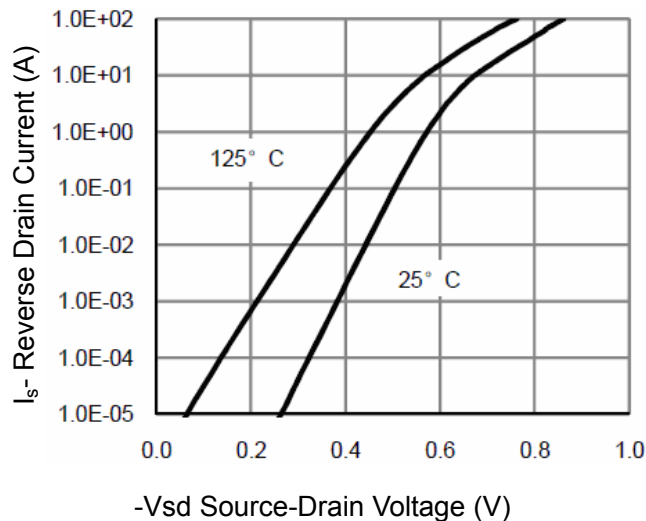
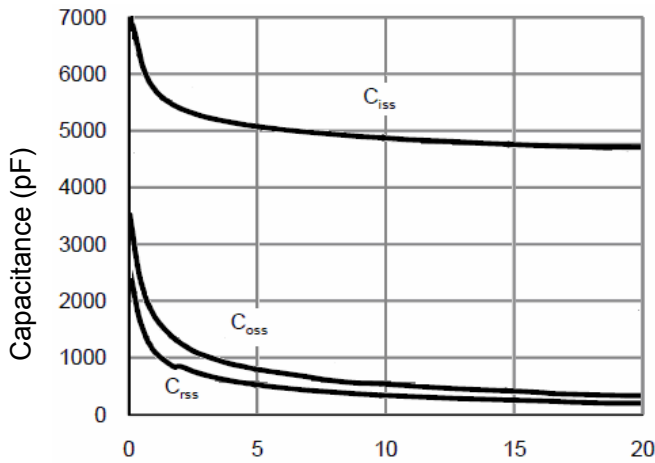
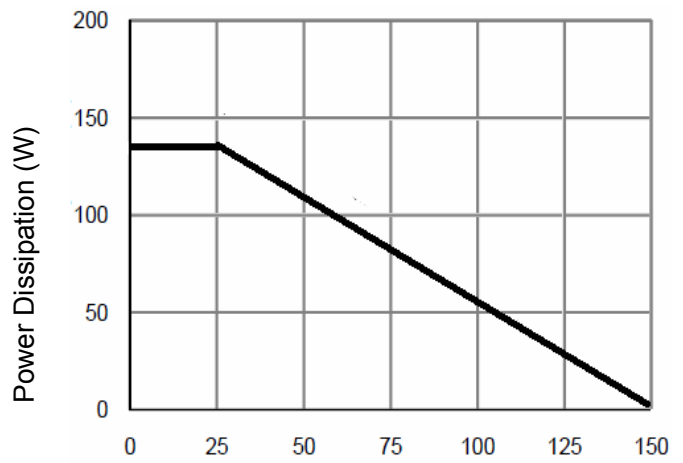


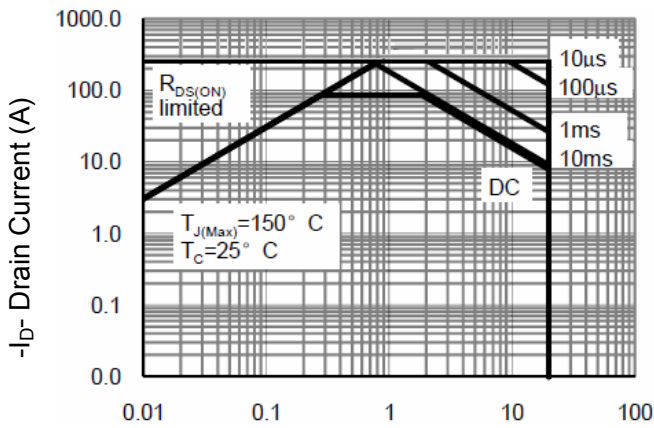
Figure 6 Source- Drain Diode Forward



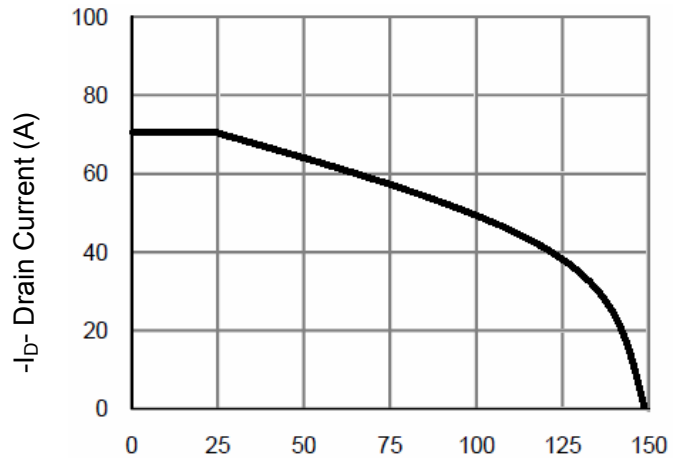
-Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



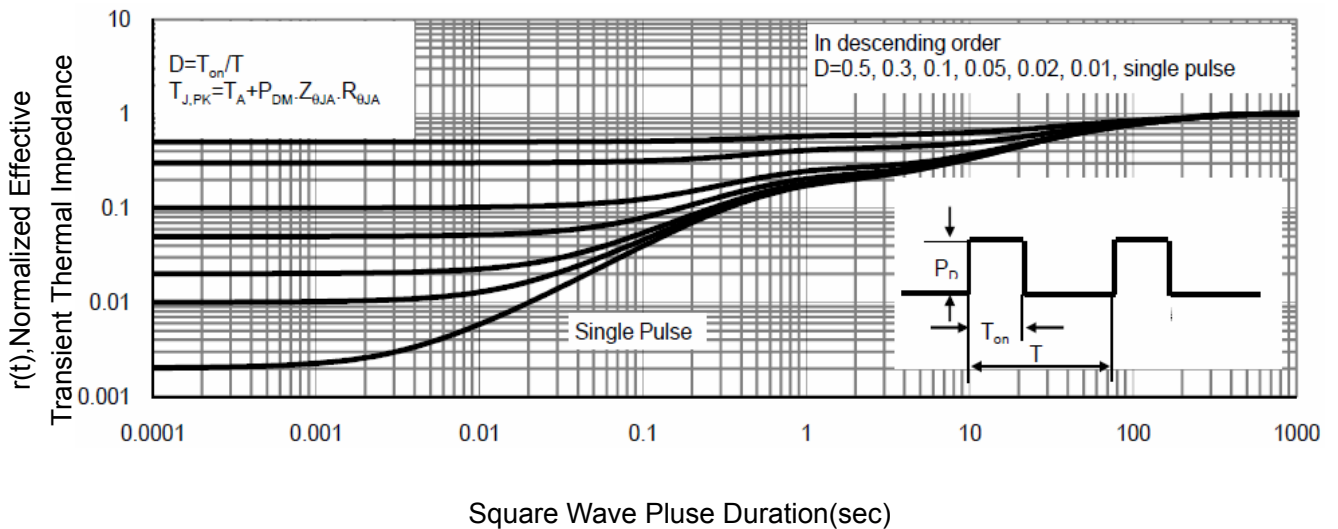
T_J-Junction Temperature(°C)
Figure 9 Power De-rating



-Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area

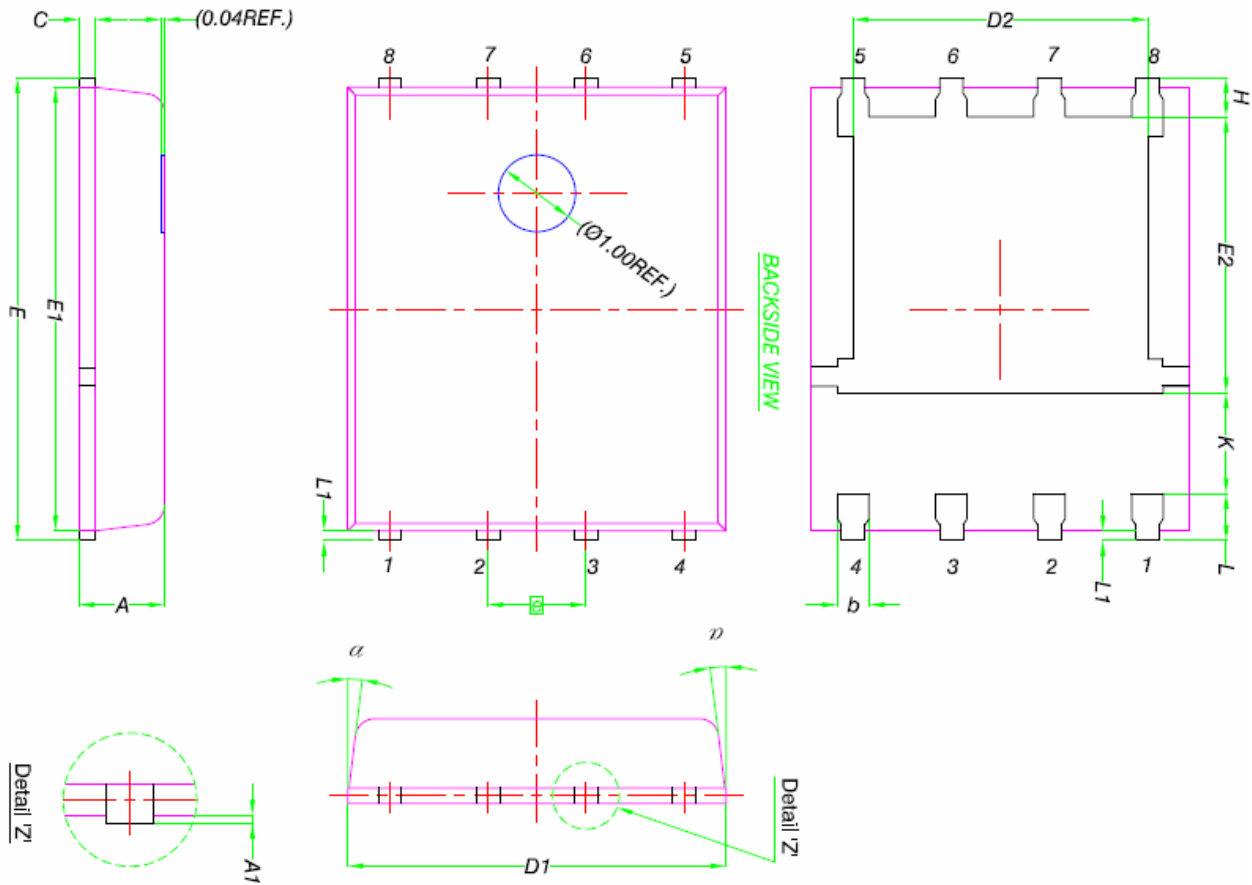


T_J-Junction Temperature(°C)
Figure 10 -Current De-rating

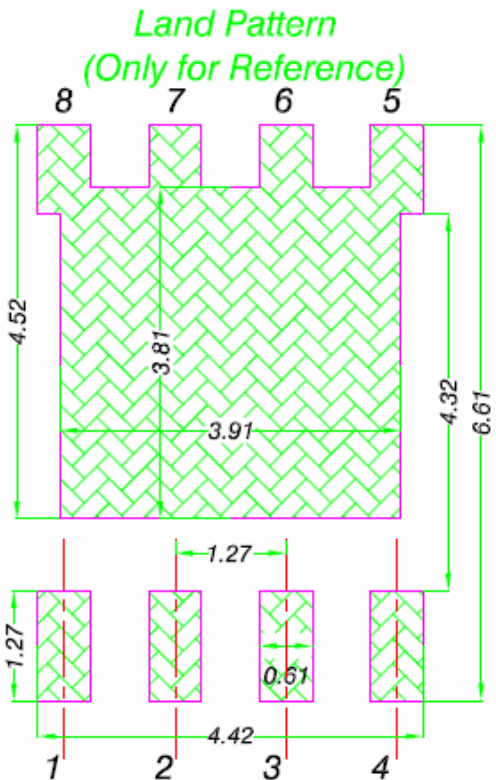


Square Wave Pulse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°



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